

Molecular Flow in an Ion-Implant Vacuum System

This example considers the design of an ion implantation system. Ion implantation is used extensively in the semiconductor industry to implant dopants into wafers. Within an ion implanter ions generated within an ion source are accelerated by an electric field to achieve the desired implant energy. Ions of the correct charge state are selected by means of a separation magnet which bends the ion beam to ensure that ions of a particular charge to mass ratio are the only ones which reach the wafer. The energy dose and angle of the ion beam are both key parameters for the process. This part of the system is known as the corrector.

Usually it is desired that only selected regions of the wafer are implanted. This is achieved by masking parts of the wafer with an organic photoresist, to produce the desired pattern. Unfortunately, the photoresist itself emits gas molecules as a result of the beam striking it. These molecules can interact with the ion beam and produce species with undesired charge to mass ratios at different points along the beam path. Some of these species may reach the wafer, degrading the uniformity of the implant, which is highly undesirable. Additionally, these ions may also effect the accuracy of measurements of the implant dose. A key requirement for the system is that the number density of the outgassing molecules for the wafer is low within the beam line.

This example shows how to model an ion implantation system using the Molecular Flow interface. Because it is interactions of outgassing molecules with the beam that produce undesirable species, the average number density of these molecules along the beam path is used as a figure of merit to evaluate the design. Furthermore, because the angle of the wafer to the beam can be modified, the figure of merit must be computed as a function of wafer angle, with rotation about one axis.

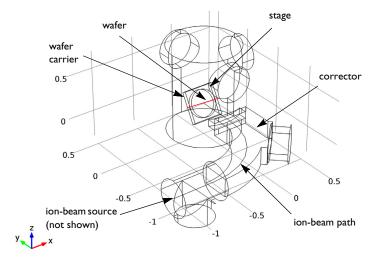


Figure 1: Model geometry. Key components of the system are labeled. The red line through the center of the wafer carrier indicates the axis of rotation of the carrier.

Note: This model is motivated by Ref. 1. However, it is important to note that there are significant differences between the pressure and number density computed by the Molecular Flow interface and those computed in the radiation analogy, which is used in Ref. 1. The COMSOL Multiphysics software computes these quantities accurately, whilst the radiation analogy uses an approximate technique to compute the number density and pressure which can result in misleading, incorrect, answers.

Model Definition

The model geometry is shown in Figure 1. The wafer is positioned on a carrier plate which is rotated about an axis through its center to achieve different implant angles. The carrier plate is mounted in a chamber that is pumped by three large cryopumps, on cylindrical vacuum ports. These pumps have a pump speed of $12,000 \, l/s$. In this model outgassing of only one species from the wafer (H_2) is considered: multiple species can be modeled by adding additional molecular flow interfaces. It is assumed that the outgassing across the wafer surface is uniform and that the total gas emitted is $30 \, \text{sccm}$. The vacuum path through the corrector magnetic field enters the main chamber opposite the wafer, and is

pumped by a turbomolecular pump on a cylindrical port midway down the corrector, with a pump speed of 1500 l/s and an additional cryopump at the start of the beam path, with a pump speed of 12,000 l/s. There is an aperture at the entrance to the chamber which reduces the flux that enters the corrector. The angle of the wafer normal to the ion beam is swept from 0° to 60° in 20° steps, as the wafer is rotated about the horizontal axis through its center, as shown in Figure 1. All other surfaces in the model are walls.

Results and Discussion

The molecular flux at the surfaces of the vacuum chamber is shown in Figure 2, for wafer normal angles of 0° and 40° to the beam.

The shadowing effect of the wafer support is evident at both wafer angles shown in Figure 2. It is also clear that more flux enters the beam line when the wafer normal is parallel to the beam because the line of sight with the beam line is then parallel to the wafer normal. The number density along the beam path is shown in Figure 3 for each of the angles solved for. The number density increases along the beam path toward the wafer, with strong changes in gradient as the beam passes through different apertures. Note that in the immediate vicinity of the wafer the number density is not computed accurately (this is difficult to see from the plot below, but zooming into the plot at the end of the beam shows issues in the results for elements adjacent to the surface). This is a result of numerical issues when computing the number density very close to a source surface within the domain.

The average number density along the beam path within the corrector can be used as figure of merit for the system design. This quantity is plotted against the angle of the wafer normal to the beam line in Figure 4. The average flux in the corrector is reduced by rotating the wafer normal away from the beam line with a 10% reduction occurring over the full angular range. Rotating the wafer in this manner can therefore result in improved performance of the implanter.

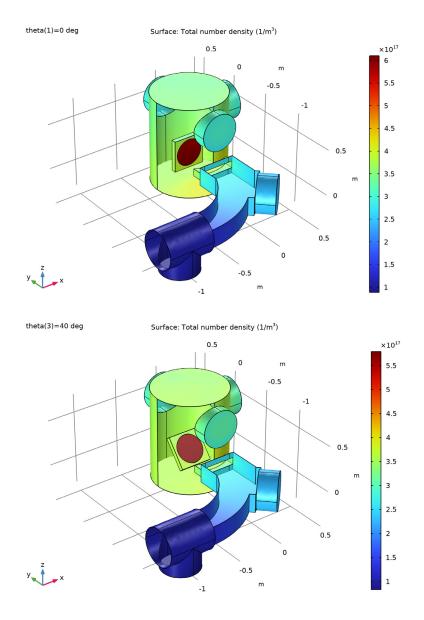


Figure 2: Pressure on the surface of the ion implanter, with the wafer normal at 0° (top) and 40° (bottom) to the beam path.

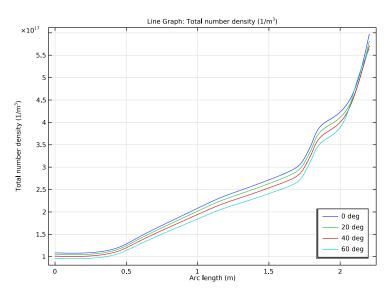


Figure 3: The number density as a function of position along the beam line.

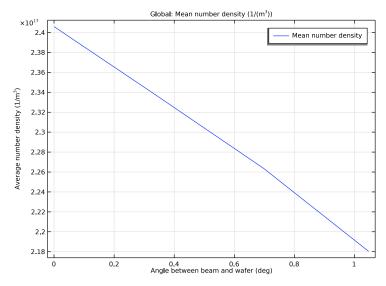


Figure 4: Plot of the average number density along the beam line as a function of the wafer normal angle to the incoming beam.

Reference

1. M.R. LaFontaine, N. Tokoro, P. Murphy, and D. Holbrook, "Modelling Photoresist Outgassing Pressure Distribution Using the Finite Element Method," Proc. Conference on Ion Implantation Technology, IEEE Press, pp. 247-250, 2000.

Notes About the COMSOL Implementation

The model is straightforward to set up using the Molecular Flow interface. The vacuum pump boundary condition is used for the pumps and the outgassing wall boundary condition is used for the wafer surface. The geometry for the vacuum system is imported, but the wafer and its carrier are generated within COMSOL Multiphysics so that the angle to the beam line can be easily parameterized.

Application Library path: Molecular_Flow_Module/Industrial_Applications/ ion implanter

Modeling Instructions

From the File menu, choose New.

NEW

In the New window, click Model Wizard.

MODEL WIZARD

- I In the Model Wizard window, click **3D**.
- 2 In the Select Physics tree, select Fluid Flow>Rarefied Flow>Free Molecular Flow (fmf).
- 3 Click Add.
- 4 Click Study.
- 5 In the Select Study tree, select General Studies>Stationary.
- 6 Click M Done.

GEOMETRY I

Insert the prepared geometry sequence from file. You can read the instructions for creating the geometry in the appendix.

- I In the Geometry toolbar, click Insert Sequence and choose Insert Sequence.
- 2 Browse to the model's Application Libraries folder and double-click the file ion implanter geom sequence.mph.
- 3 In the Geometry toolbar, click **Build All**.

GLOBAL DEFINITIONS

Define parameters for the pump speeds. The parameter theta for the wafer angle was automatically defined when the geometry sequence was loaded.

Parameters 1

- I In the Model Builder window, under Global Definitions click Parameters I.
- 2 In the Settings window for Parameters, locate the Parameters section.
- **3** In the table, enter the following settings:

Name	Expression	Value	Description
pumpspeedcryo	12000[1/s]	12 m³/s	Pump speed for cryopumps
pumpspeedturbo	1500[l/s]	1.5 m³/s	Pump speed for turbopump

Add a nonlocal average coupling to compute the average number density along the beam line.

DEFINITIONS

Beam line

- I In the **Definitions** toolbar, click **\(\frac{1}{2} \) Explicit**.
- 2 In the Settings window for Explicit, locate the Input Entities section.
- 3 From the Geometric entity level list, choose Edge.
- 4 Select Edges 6, 33, and 103 only.
- 5 In the Label text field, type Beam line.

Average I (aveob I)

- I In the Definitions toolbar, click Nonlocal Couplings and choose Average.
- 2 In the Settings window for Average, locate the Source Selection section.
- 3 From the Geometric entity level list, choose Edge.
- 4 Click the Wireframe Rendering button in the Graphics toolbar.
- 5 From the Selection list, choose Beam line.

Set the physics interface to simulate free molecular flow of hydrogen.

FREE MOLECULAR FLOW (FMF)

Molecular Flow 1

- I In the Model Builder window, under Component I (compl)>Free Molecular Flow (fmf) click Molecular Flow I.
- 2 In the Settings window for Molecular Flow, locate the Molecular Weight of Species section.
- **3** In the $M_{\rm n.G}$ text field, type 0.002[kg/mol].

Define the wafer as an outgassing wall that releases 30 sccm of hydrogen.

Wall 2

- I In the Physics toolbar, click **Boundaries** and choose Wall.
- 2 Select Boundary 42 only.
- 3 In the Settings window for Wall, locate the Wall Type section.
- 4 From the Wall type list, choose Outgassing wall.
- 5 Locate the Flux section. From the Outgoing flux list, choose Number of SCCM units.
- **6** In the $Q_{\text{sccm.G}}$ text field, type 30.

Set up the vacuum pumps.

Vacuum Pump I

- I In the Physics toolbar, click **Boundaries** and choose **Vacuum Pump**.
- 2 In the Settings window for Vacuum Pump, locate the Vacuum Pump section.
- 3 From the Specify pump flux list, choose Pump speed.
- 4 Select Boundary 55 only.
- **5** In the $S_{\rm G}$ text field, type pumpspeedturbo.

Vacuum Pump 2

- I In the Physics toolbar, click **Boundaries** and choose **Vacuum Pump**.
- 2 In the Settings window for Vacuum Pump, locate the Vacuum Pump section.
- 3 From the Specify pump flux list, choose Pump speed.
- 4 Select Boundary 8 only.
- **5** In the S_G text field, type pumpspeedcryo.

Vacuum Pump 3

- I Right-click Vacuum Pump 2 and choose Duplicate.
- 2 In the Settings window for Vacuum Pump, locate the Boundary Selection section.
- 3 Click Clear Selection.

4 Select Boundary 25 only.

Vacuum Pump 4

- I Right-click Vacuum Pump 3 and choose Duplicate.
- 2 In the Settings window for Vacuum Pump, locate the Boundary Selection section.
- 3 Click Clear Selection.
- 4 Select Boundary 70 only.

Vacuum Pump 5

- I Right-click Vacuum Pump 4 and choose Duplicate.
- 2 In the Settings window for Vacuum Pump, locate the Boundary Selection section.
- 3 Click Clear Selection.
- 4 Select Boundary 33 only.

Number Density Reconstruction I

- I In the Physics toolbar, click Edges and choose Number Density Reconstruction.
- 2 In the Settings window for Number Density Reconstruction, locate the Edge Selection section.
- 3 From the Selection list, choose Beam line.

Next create the mesh. Add a fine mesh along the beam line.

MESH I

Edge I

- I In the Mesh toolbar, click A Boundary and choose Edge.
- 2 In the Settings window for Edge, locate the Edge Selection section.
- 3 From the Selection list, choose Beam line.

Use a very fine mesh along the beam line.

Size 1

- I Right-click **Edge** I and choose **Size**.
- 2 In the Settings window for Size, locate the Element Size section.
- 3 Click the **Custom** button.
- 4 Locate the Element Size Parameters section.
- 5 Select the Maximum element size check box. In the associated text field, type 0.005.

Change the global mesh size setting to refine the mesh.

Size

- I In the Model Builder window, under Component I (compl)>Mesh I click Size.
- 2 In the Settings window for Size, locate the Element Size section.
- 3 From the Predefined list, choose Extra fine.

Add a free triangular surface mesh. This will inherit the global mesh size setting.

Free Triangular I

- I In the Mesh toolbar, click A Boundary and choose Free Triangular.
- 2 In the Settings window for Free Triangular, locate the Boundary Selection section.
- 3 From the Selection list, choose All boundaries.
- 4 Click Build All.

The domain does not need to be meshed since the interface solves equations only on the surfaces of the model. Note that it is possible to mesh surfaces, edges, and points (as in this model) or to mesh the entire domain. These two approaches cannot be mixed (doing so may lead to incorrect results in some cases).

Set up a parametric sweep over the wafer angle.

STUDY I

Parametric Sweep

- I In the Study toolbar, click Parametric Sweep.
- 2 In the Settings window for Parametric Sweep, locate the Study Settings section.
- 3 Click + Add.
- 4 In the table, enter the following settings:

Parameter name	Parameter value list	Parameter unit
theta (Wafer angle)		deg

- 5 Click Range.
- 6 In the Range dialog box, type 0 in the Start text field.
- 7 In the Step text field, type 20.
- **8** In the **Stop** text field, type 60.
- 9 Click Add.
- 10 In the Study toolbar, click **Compute**.

RESULTS

Incident Molecular Flux (fmf)

Duplicate the solution dataset and apply a boundary selection in order to see inside the vacuum chamber.

Study I/Parametric Solutions I (3) (sol2)

- I In the Model Builder window, expand the Results>Datasets node.
- 2 Right-click Results>Datasets>Study I/Parametric Solutions I (sol2) and choose Duplicate.

Selection

- I In the Model Builder window, right-click Study I/Parametric Solutions I (3) (sol2) and choose Selection.
- 2 In the Settings window for Selection, locate the Geometric Entity Selection section.
- 3 From the Geometric entity level list, choose Boundary.
- **4** From the **Selection** list, choose **Postprocessing**.

Update the default plots to use the new dataset.

Incident Molecular Flux (fmf)

- I In the Model Builder window, under Results click Incident Molecular Flux (fmf).
- 2 In the Settings window for 3D Plot Group, locate the Data section.
- 3 From the Dataset list, choose Study I/Parametric Solutions I (3) (sol2).

Total Number Density (fmf)

- I In the Model Builder window, click Total Number Density (fmf).
- 2 In the Settings window for 3D Plot Group, locate the Data section.
- 3 From the Dataset list, choose Study I/Parametric Solutions I (3) (sol2).

Total Pressure (fmf)

- I In the Model Builder window, click Total Pressure (fmf).
- 2 In the Settings window for 3D Plot Group, locate the Data section.
- 3 From the Dataset list, choose Study I/Parametric Solutions I (3) (sol2).

Reproduce the results shown in Figure 2.

Total Number Density (fmf)

- I In the Model Builder window, click Total Number Density (fmf).
- 2 In the Settings window for 3D Plot Group, locate the Data section.
- 3 From the Parameter value (theta (deg)) list, choose 0.

4 In the Total Number Density (fmf) toolbar, click **Plot**.

Repeat steps 3 and 4, this time selecting an angle of 40 degrees.

Compare the resulting plot with that in Figure 2.

Create a plot of the number density along the beam path.

Number Density Along Beam Line

- I In the Home toolbar, click Add Plot Group and choose ID Plot Group.
- 2 In the **Settings** window for **ID Plot Group**, type Number Density Along Beam Line in the **Label** text field.
- 3 Locate the Data section. From the Dataset list, choose Study 1/ Parametric Solutions 1 (2) (sol2).
- 4 Locate the Legend section. From the Position list, choose Lower right.

Line Graph 1

- I Right-click Number Density Along Beam Line and choose Line Graph.
- 2 In the Settings window for Line Graph, locate the Selection section.
- 3 From the Selection list, choose Beam line.
- 4 Click Replace Expression in the upper-right corner of the y-Axis Data section. From the menu, choose Component I (compl)>Free Molecular Flow>Number density>fmf.ntot Total number density I/m³.
- **5** Click to expand the **Legends** section. Select the **Show legends** check box.
- 6 Click to expand the Quality section. From the Resolution list, choose No refinement.

Compare the resulting plot with that in Figure 3.

Finally, plot the mean number density along the beam line, as a function of wafer angle.

Average Number Density vs. Wafer Angle

- I In the Home toolbar, click Add Plot Group and choose ID Plot Group.
- 2 In the Settings window for ID Plot Group, type Average Number Density vs. Wafer Angle in the Label text field.
- 3 Locate the Data section. From the Dataset list, choose Study I/ Parametric Solutions I (2) (sol2).
- 4 Locate the **Plot Settings** section.
- 5 Select the **x-axis label** check box. In the associated text field, type Angle between beam and wafer (deg).

6 Select the y-axis label check box. In the associated text field, type Average number density (1/m < sup > 3 < / sup >).

Global I

- I Right-click Average Number Density vs. Wafer Angle and choose Global.
- 2 In the Settings window for Global, locate the y-Axis Data section.
- **3** In the table, enter the following settings:

Expression	Unit	Description
aveop1(fmf.ntot)	1/(m^3)	Mean number density

- 4 Locate the x-Axis Data section. From the Parameter list, choose Expression.
- 5 In the Expression text field, type theta.
- 6 In the Average Number Density vs. Wafer Angle toolbar, click **Plot**. Compare the resulting plot with that in Figure 4.

Appendix - Geometry Instructions

From the File menu, choose New.

In the New window, click Blank Model.

GLOBAL DEFINITIONS

Parameters 1

- I In the Model Builder window, under Global Definitions click Parameters I.
- 2 In the Settings window for Parameters, locate the Parameters section.
- **3** In the table, enter the following settings:

Name	Expression	Value	Description
theta	30[deg]	0.5236 rad	Wafer angle

ADD COMPONENT

In the **Home** toolbar, click **Add Component** and choose **3D**.

GEOMETRY I

Cylinder I (cyll)

- I In the Geometry toolbar, click Cylinder.
- 2 In the Settings window for Cylinder, locate the Size and Shape section.
- 3 In the Radius text field, type 0.4.
- 4 Locate the **Position** section. In the **z** text field, type -0.3.

Cylinder 2 (cyl2)

- I In the Geometry toolbar, click (Cylinder.
- 2 In the Settings window for Cylinder, locate the Size and Shape section.
- 3 In the Radius text field, type 0.2.
- 4 In the Height text field, type 0.5.
- **5** Locate the **Position** section. In the **y** text field, type -0.5.
- 6 In the z text field, type 0.45.
- 7 Locate the Axis section. From the Axis type list, choose y-axis.

Rotate I (rot1)

- I In the Geometry toolbar, click \(\sum_{\text{transforms}} \) Transforms and choose Rotate.
- **2** Select the object **cyl2** only.
- 3 In the Settings window for Rotate, locate the Rotation section.
- 4 In the Angle text field, type 0,90,180.

Cylinder 3 (cyl3)

- I In the Geometry toolbar, click Cylinder.
- 2 In the Settings window for Cylinder, locate the Size and Shape section.
- 3 In the Radius text field, type 0.2.
- 4 In the Height text field, type 0.5.
- **5** Locate the **Position** section. In the **x** text field, type -1.3.
- 6 In the y text field, type -1.25.
- 7 Locate the Axis section. From the Axis type list, choose x-axis.

Cylinder 4 (cyl4)

- I In the Geometry toolbar, click Cylinder.
- 2 In the Settings window for Cylinder, locate the Size and Shape section.
- 3 In the Radius text field, type 0.2.

- 4 In the Height text field, type 0.3.
- **5** Locate the **Position** section. In the **x** text field, type -1.05.
- 6 In the y text field, type -1.25.
- 7 In the z text field, type -0.3.

Block I (blk I)

- I In the Geometry toolbar, click Block.
- 2 In the Settings window for Block, locate the Size and Shape section.
- 3 In the Width text field, type 0.4.
- 4 In the **Depth** text field, type 0.2.
- 5 In the Height text field, type 0.08.
- 6 Locate the **Position** section. In the **x** text field, type -0.2.
- 7 In the y text field, type -0.45.
- 8 In the z text field, type -0.04.

Work Plane I (wbl)

- I In the Geometry toolbar, click Work Plane.
- 2 In the Settings window for Work Plane, locate the Selections of Resulting Entities section.
- **3** Select the **Resulting objects selection** check box.
- 4 From the Show in physics list, choose All levels.

Work Plane I (wp I)>Plane Geometry

In the Model Builder window, click Plane Geometry.

Work Plane I (wbl)>Circle I (cl)

- I In the Work Plane toolbar, click () Circle.
- 2 In the Settings window for Circle, locate the Size and Shape section.
- 3 In the Radius text field, type 0.8.
- 4 In the Sector angle text field, type 90.
- **5** Locate the **Position** section. In the **xw** text field, type -0.8.
- 6 In the yw text field, type -0.45.
- 7 Locate the Rotation Angle section. In the Rotation text field, type -90.
- 8 Locate the **Object Type** section. From the **Type** list, choose **Curve**.

Work Plane I (wbl)>Rectangle I (rl)

I In the Work Plane toolbar, click Rectangle.

- 2 In the Settings window for Rectangle, locate the Object Type section.
- 3 From the Type list, choose Curve.
- 4 Locate the Size and Shape section. In the Width text field, type 1.3.
- 5 In the **Height** text field, type 1.25.
- 6 Locate the Position section. In the xw text field, type -1.3.
- 7 In the yw text field, type -1.25.

Work Plane I (wpl)>Union I (unil)

- I In the Work Plane toolbar, click Booleans and Partitions and choose Union.
- 2 Click in the **Graphics** window and then press Ctrl+A to select both objects.
- 3 In the Settings window for Union, click | Build Selected.

Work Plane I (wpl)>Delete Entities I (dell)

- I In the Work Plane toolbar, click **Delete**.
- 2 In the Settings window for Delete Entities, locate the Entities or Objects to Delete section.
- 3 From the Geometric entity level list, choose Boundary.
- **4** On the object **unil**, select Boundaries 1 and 3–7 only.

Work Plane 2 (wb2)

- I In the Model Builder window, under Component I (compl)>Geometry I right-click Work Plane I (wpl) and choose Work Plane.
- 2 In the Settings window for Work Plane, locate the Plane Definition section.
- 3 In the **z-coordinate** text field, type 0.1.

Work Plane 2 (wp2)>Plane Geometry

In the Model Builder window, click Plane Geometry.

Work Plane 2 (wp2)>Circle 1 (c1)

- I In the Work Plane toolbar, click Circle.
- 2 In the Settings window for Circle, locate the Object Type section.
- **3** From the **Type** list, choose **Curve**.
- 4 Locate the Size and Shape section. In the Radius text field, type 0.95.
- 5 In the Sector angle text field, type 90.
- 6 Locate the Position section. In the xw text field, type -0.8.
- 7 In the yw text field, type -0.45.
- 8 Locate the Rotation Angle section. In the Rotation text field, type -90.

9 Click to expand the **Layers** section. In the table, enter the following settings:

Layer name	Thickness (m)
Layer 1	0.3

10 Click | Build Selected.

Work Plane 2 (wp2)>Delete Entities 1 (del1)

- I In the Work Plane toolbar, click **Delete**.
- 2 In the Settings window for Delete Entities, locate the Entities or Objects to Delete section.
- 3 From the Geometric entity level list, choose Boundary.
- **4** On the object **c1**, select Boundaries 1 and 2 only.

Work Plane 2 (wp2)>Rectangle 1 (r1)

- I In the Work Plane toolbar, click Rectangle.
- 2 In the Settings window for Rectangle, locate the Size and Shape section.
- 3 In the Width text field, type 0.4.
- 4 In the **Height** text field, type 0.36.
- **5** Locate the **Position** section. In the **xw** text field, type -0.2.
- 6 In the yw text field, type -0.81.

Work Plane 2 (wp2)>Rectangle 2 (r2)

- I In the Work Plane toolbar, click Rectangle.
- 2 In the Settings window for Rectangle, locate the Size and Shape section.
- **3** In the **Width** text field, type **0.5**.
- **4** In the **Height** text field, type **0.25**.
- **5** Locate the **Position** section. In the **xw** text field, type -0.12.
- 6 In the yw text field, type -1.2.
- 7 Locate the Rotation Angle section. In the Rotation text field, type 45.

Work Plane 2 (wp2)>Union I (unil)

- I In the Work Plane toolbar, click Booleans and Partitions and choose Union.
- 2 Click in the **Graphics** window and then press Ctrl+A to select all objects.
- 3 In the Settings window for Union, locate the Union section.
- 4 Clear the Keep interior boundaries check box.

Extrude I (extI)

- I In the Model Builder window, under Component I (compl)>Geometry I right-click Work Plane 2 (wp2) and choose Extrude.
- 2 In the Settings window for Extrude, locate the Distances section.
- **3** In the table, enter the following settings:

Distances (m)

0.2

4 Select the Reverse direction check box.

Work Plane 3 (wb3)

- I In the Geometry toolbar, click Work Plane.
- 2 In the Settings window for Work Plane, locate the Plane Definition section.
- 3 From the Plane type list, choose Face parallel.
- 4 On the object ext1, select Boundary 10 only.

Work Plane 3 (wp3)>Plane Geometry

In the Model Builder window, click Plane Geometry.

Work Plane 3 (wp3)>Circle 1 (c1)

- I In the Work Plane toolbar, click Circle.
- 2 In the Settings window for Circle, locate the Size and Shape section.
- 3 In the Radius text field, type 0.2.

Extrude 2 (ext2)

- I In the Model Builder window, under Component I (compl)>Geometry I right-click Work Plane 3 (wp3) and choose Extrude.
- 2 In the Settings window for Extrude, locate the Distances section.
- 3 In the table, enter the following settings:

Distances (m)

0.2

Union I (uni I)

- I In the Geometry toolbar, click Booleans and Partitions and choose Union.
- 2 Select the objects blk1, cyl1, cyl3, cyl4, ext1, ext2, rot1(1), rot1(2), and rot1(3) only.
- 3 In the Settings window for Union, locate the Union section.
- 4 Clear the Keep interior boundaries check box.

Work Plane 4 (wp4)

- I In the Geometry toolbar, click Work Plane.
- 2 In the Settings window for Work Plane, locate the Plane Definition section.
- 3 From the Plane type list, choose Coordinates.
- 4 In row Point 3, set y to sin(theta).
- 5 In row Point 3, set z to cos (theta).

Work Plane 4 (wp4)>Plane Geometry

In the Model Builder window, click Plane Geometry.

Work Plane 4 (wp4)>Circle I (c1)

- I In the Work Plane toolbar, click (Circle.
- 2 In the Settings window for Circle, locate the Size and Shape section.
- 3 In the Radius text field, type 0.15.

Work Plane 4 (wb4)>Square 1 (sq1)

- I In the Work Plane toolbar, click Square.
- 2 In the Settings window for Square, locate the Size section.
- 3 In the Side length text field, type 0.35.
- 4 Locate the **Position** section. From the **Base** list, choose **Center**.

Extrude 3 (ext3)

- I In the Model Builder window, under Component I (compl)>Geometry I right-click Work Plane 4 (wp4) and choose Extrude.
- 2 In the Settings window for Extrude, locate the Distances section.
- **3** In the table, enter the following settings:

Distances (m) 0.05

4 Select the Reverse direction check box.

Difference I (dif1)

- I In the Geometry toolbar, click Booleans and Partitions and choose Difference.
- **2** Select the object **unil** only.
- 3 In the Settings window for Difference, locate the Difference section.
- 4 Click to select the Activate Selection toggle button for Objects to subtract.
- **5** Select the object **ext3** only.

Form Union (fin)

- I In the Model Builder window, click Form Union (fin).
- 2 In the Settings window for Form Union/Assembly, click | Build Selected.

Explicit Selection I (sell)

- I In the Geometry toolbar, click \(\frac{1}{2} \) Selections and choose Explicit Selection.
- 2 In the Settings window for Explicit Selection, locate the Entities to Select section.
- 3 From the Geometric entity level list, choose Boundary.
- 4 On the object fin, select Boundaries 1, 16, and 18 only.

Postprocessing

- I In the Geometry toolbar, click \(\frac{1}{2} \) Selections and choose Complement Selection.
- 2 In the Settings window for Complement Selection, locate the Geometric Entity Level section.
- 3 From the Level list, choose Boundary.
- **4** Locate the **Input Entities** section. Click **Add**.
- 5 In the Add dialog box, select Explicit Selection 1 in the Selections to invert list.
- 6 Click OK.
- 7 In the Settings window for Complement Selection, type Postprocessing in the Label text field.